

Product Description

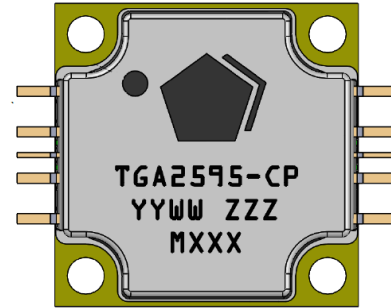
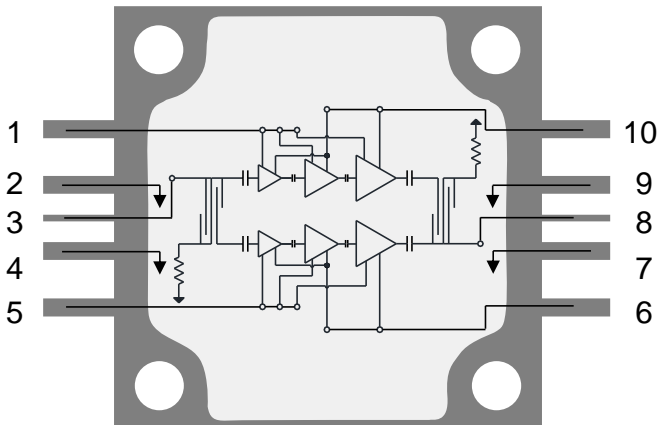
Qorvo's TGA2595-CP is a balanced Ka-Band power amplifier fabricated on Qorvo's QGaN15 0.15 um GaN on SiC process. The balanced configuration supports low return loss and improves robustness into non-ideal loads. Operating from 27.5 to 31 GHz, the TGA2595-CP achieves 39 dBm saturated output power with power-added efficiency of > 22 % and power gain of 21 dB.

The TGA2595-CP is packaged in a 10-lead 15x15 mm bolt-down package with a Cu base for superior thermal management. To simply system integration, the TGA2595-CP is fully matched to 50 ohms with integrated DC blocking capacitors on both I/O ports.

The TGA2595-CP is ideally suited for both commercial and defense satellite communications.

Lead free and RoHS compliant.

Functional Block Diagram



Product Features

- Frequency Range: 27.5 – 31 GHz
- P_{OUT} : 39 dBm ($P_{IN} = 18$ dBm)
- PAE: > 22 % ($P_{IN} = 18$ dBm)
- Power Gain: 21 dB ($P_{IN} = 18$ dBm)
- IM3 @ 30 dBm/Tone = -27 dBc
- IM5 @ 30 dBm/Tone = -46 dBc
- Bias: $V_D = +20$ V, $I_{DQ} = 560$ mA, $V_G = -2.5$ V typical
- Package Dimensions: 15.2 x 15.2 x 5.2 mm
- Package base is pure Cu offering superior thermal management

Applications

- Satellite Communications

Ordering Information

Part No.	Description
TGA2595-CP	27.5 – 31 GHz 8W GaN Power Amplifier
1095829	TGA2595-CP Evaluation Board



TGA2595-CP

27.5 – 31 GHz 8 W GaN Power Amplifier

Absolute Maximum Ratings

Parameter	Value / Range
Drain Voltage (V_D)	29.5 V
Gate Voltage Range (V_G)	-5 to 0 V
Drain Current (I_D)	2.8 A
Gate Current (I_G)	See plot at page 10
Power Dissipation (P_{DISS}), 85 °C	48 W
Input Power, CW, 50 Ω , (P_{IN})	30 dBm
Input Power, CW, VSWR 6:1, $V_D = +22$ V, 85 °C, (P_{IN})	25 dBm
Channel Temperature (T_{CH})	275 °C
Soldering Temperature (30 Seconds)	260 °C
Storage Temperature	-55 to 150 °C

Operation of this device outside the parameter ranges given above may cause permanent damage. These are stress ratings only, and functional operation of the device at these conditions is not implied.

Recommended Operating Conditions

Parameter	Min	Typ.	Max	Units
Drain Voltage (V_D)		+20		V
Drain Current, (I_{DQ})		560		mA
Drain Current, RF (I_{D_Drive})	See chart page 5			mA
Gate Voltage Range (V_G)	-2 to -2.9			V
Gate Current, RF (I_{G_Drive})	See chart page 5			mA
T_{BASE} Range	-40		+85	°C

Electrical specifications are measured at specified test conditions. Specifications are not guaranteed over all recommended operating conditions.

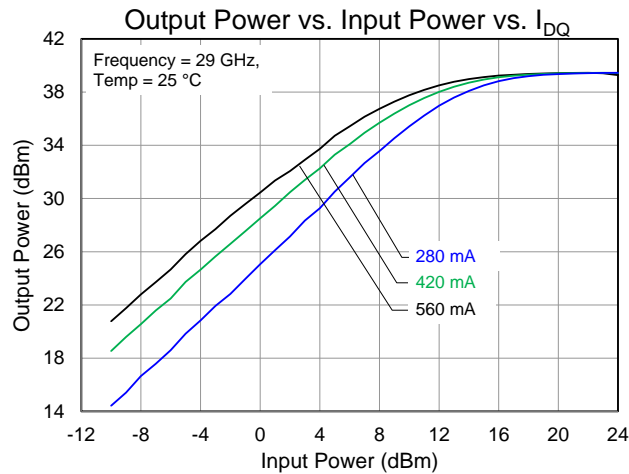
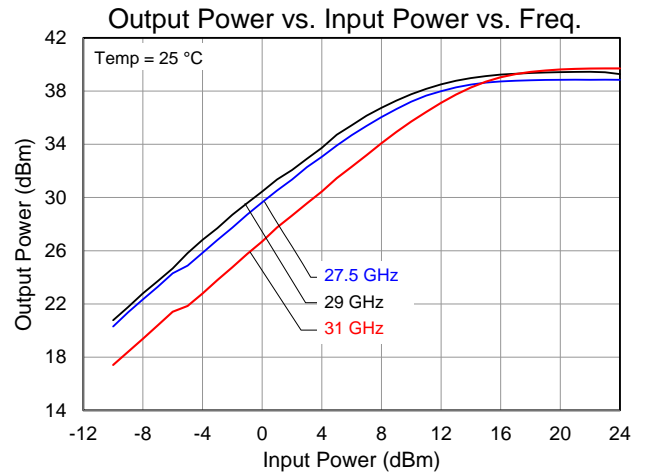
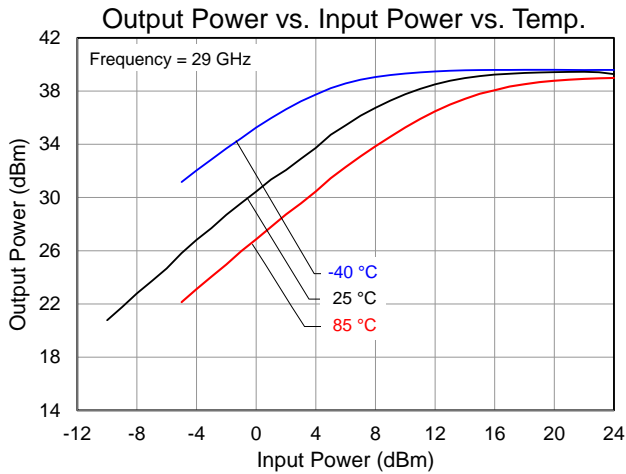
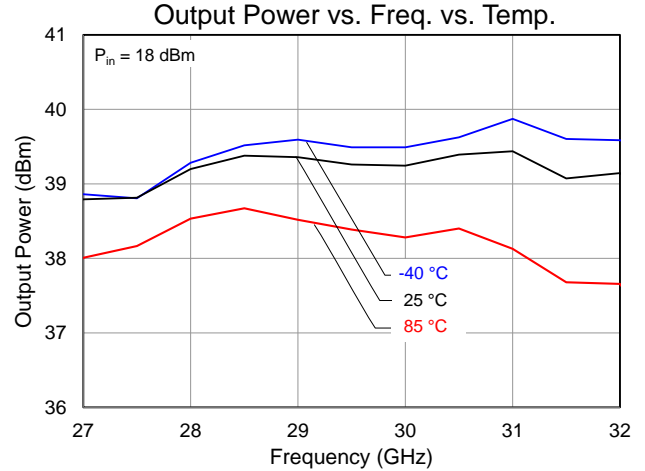
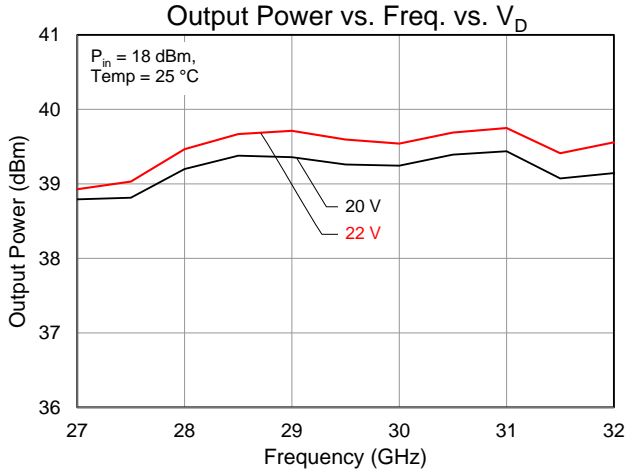
Electrical Specifications

Parameter	Min	Typ	Max	Units
Operational Frequency Range	27.5	-	31	GHz
Small Signal Gain	-	> 25	-	dB
Input Return Loss	-	> 12	-	dB
Output Return Loss	-	> 13	-	dB
Output Power (at $P_{IN} = 18$ dBm)	-	39	-	dBm
Power Added Efficiency (at $P_{IN} = 18$ dBm)	-	> 22	-	%
Power Gain (at $P_{IN} = 18$ dBm)	-	21	-	dB
IM3 @ 30 dBm/Tone	-	-27	-	dBc
IM5 @ 30 dBm/Tone	-	-46	-	dBc
Output Power Temperature Coefficient (25 °C to 85 °C only)	-	-0.01	-	dBm/°C
Recommended Operating Voltage	-	20	22	V

Test conditions unless otherwise noted: 25 °C, $V_D = +20$ V, $I_{DQ} = 560$ mA, $V_G = -2.5$ V typical.

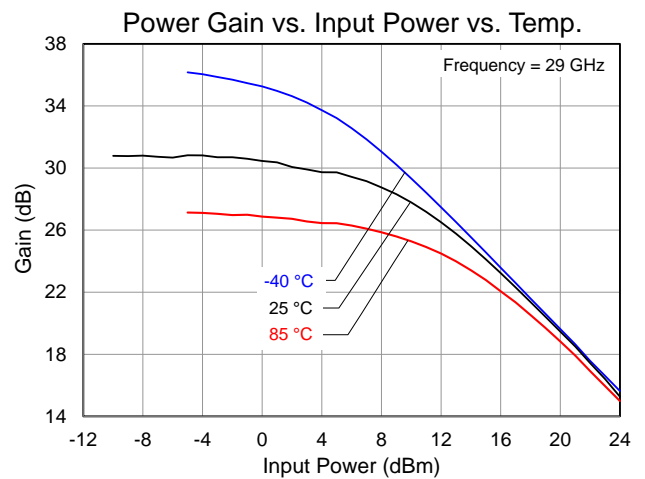
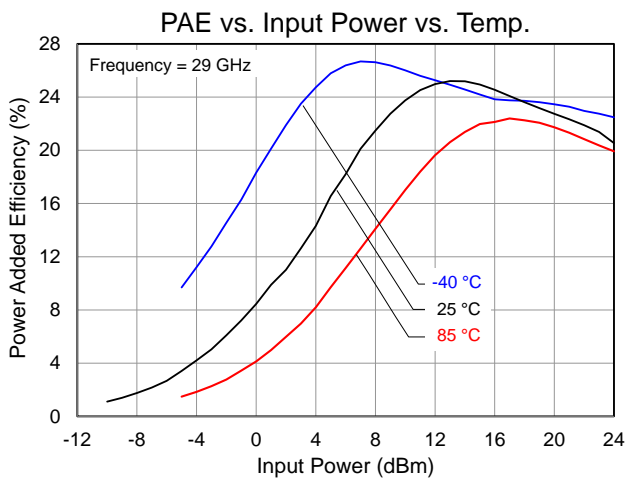
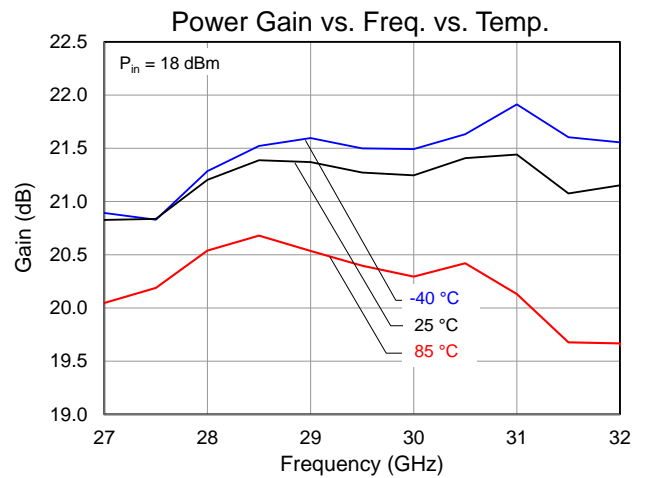
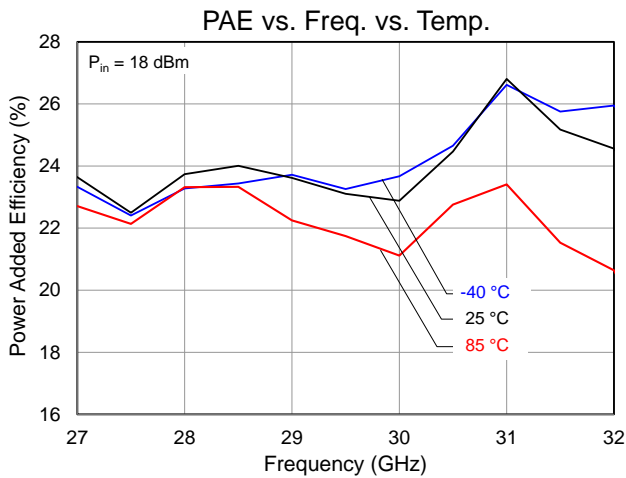
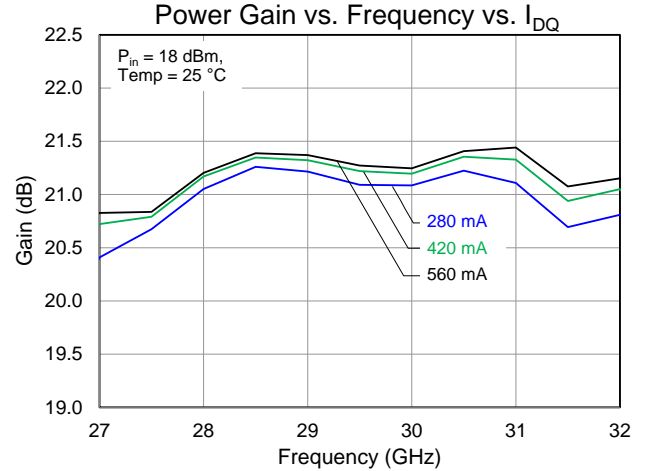
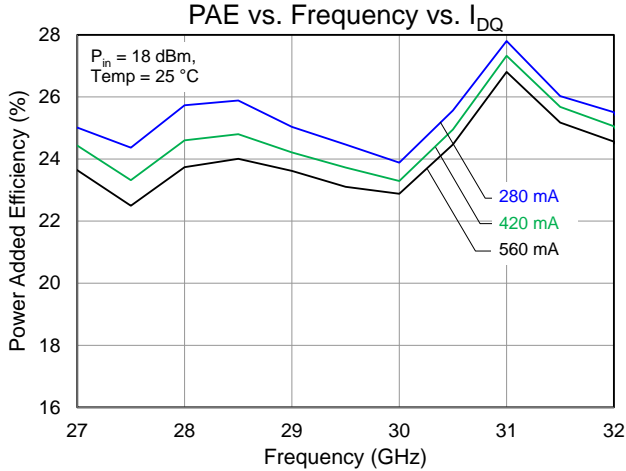
Typical Performance – Large Signal

Conditions unless otherwise specified: $V_D = +20\text{ V}$, $I_{DQ} = 560\text{ mA}$, $V_G = -2.5\text{ V}$ typical, CW.



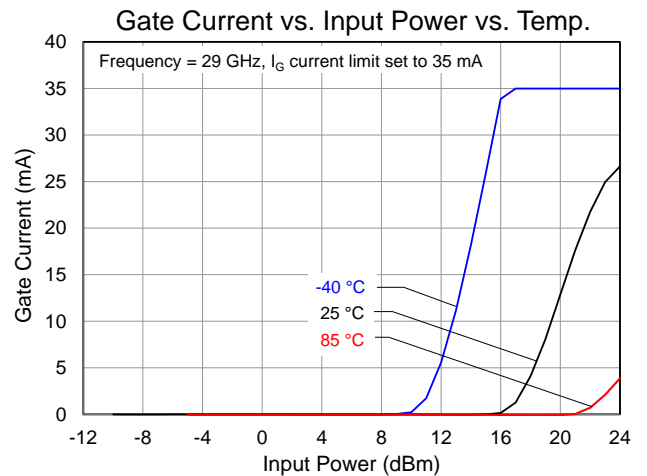
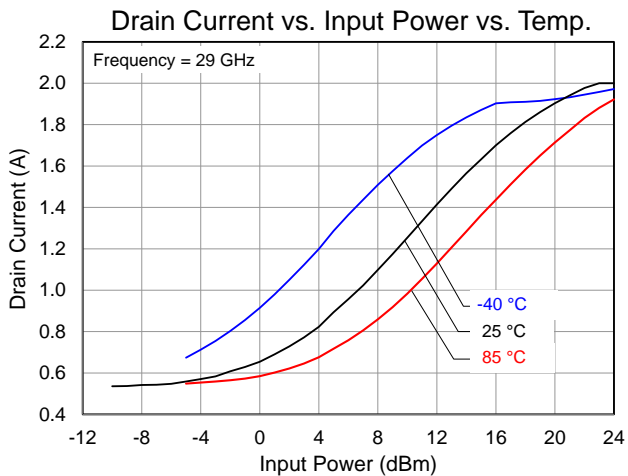
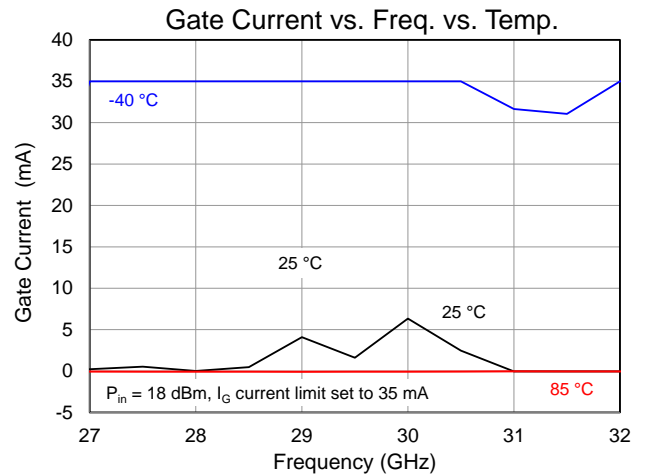
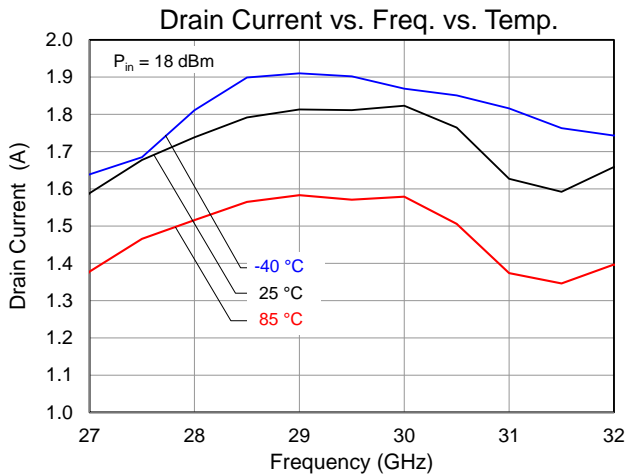
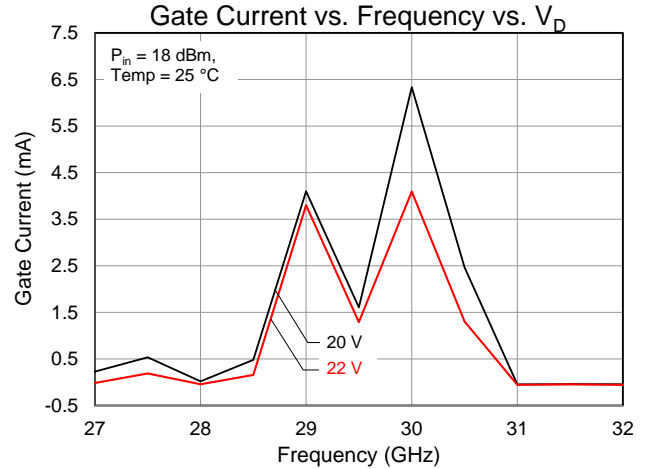
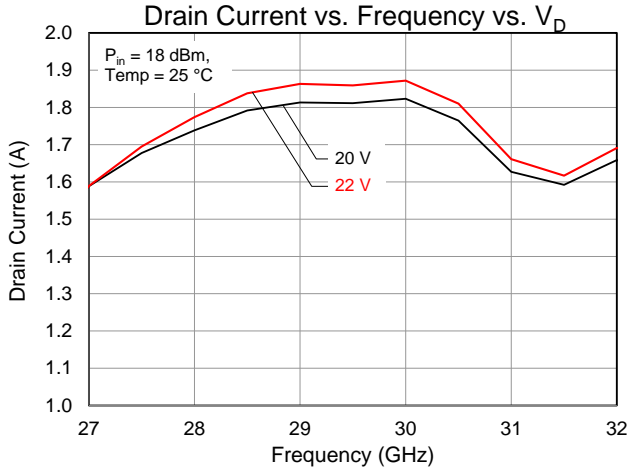
Typical Performance – Large Signal

Conditions unless otherwise specified: $V_D = +20\text{ V}$, $I_{DQ} = 560\text{ mA}$, $V_G = -2.5\text{ V}$ typical, CW.



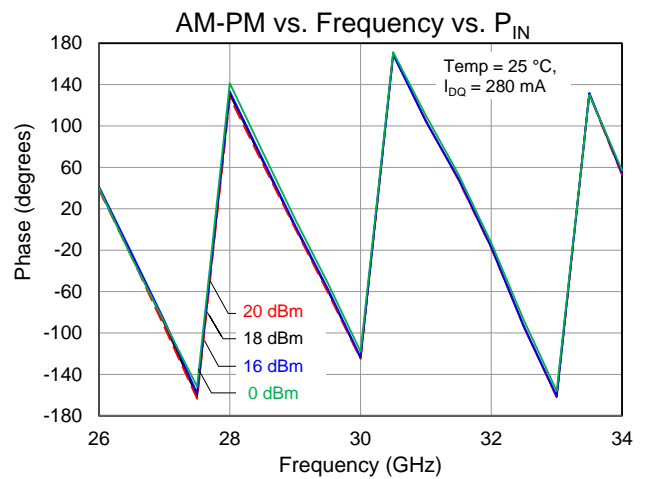
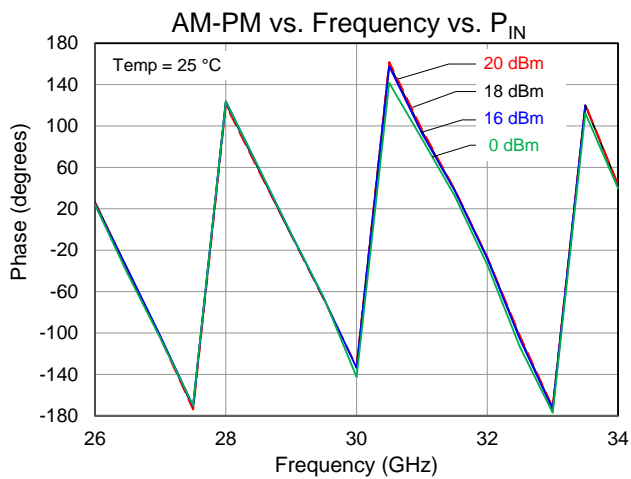
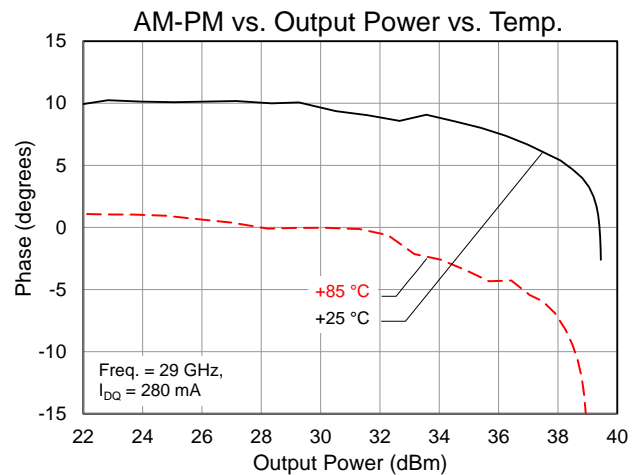
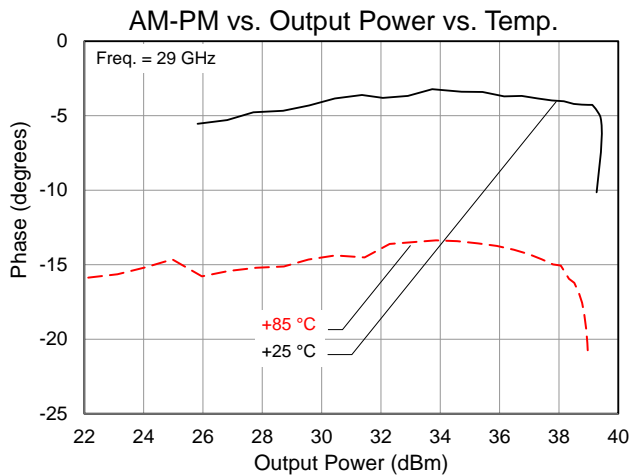
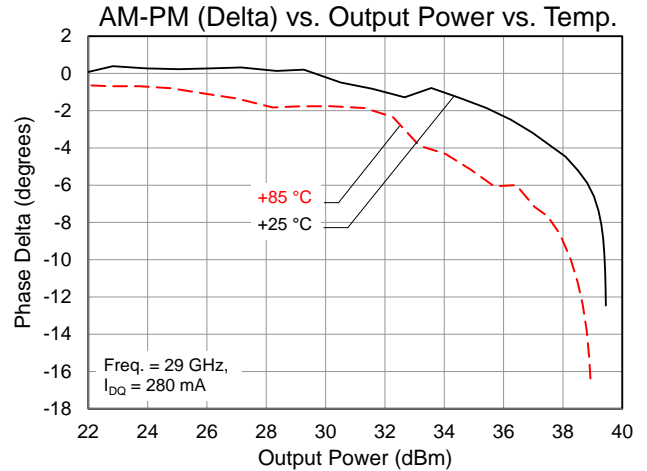
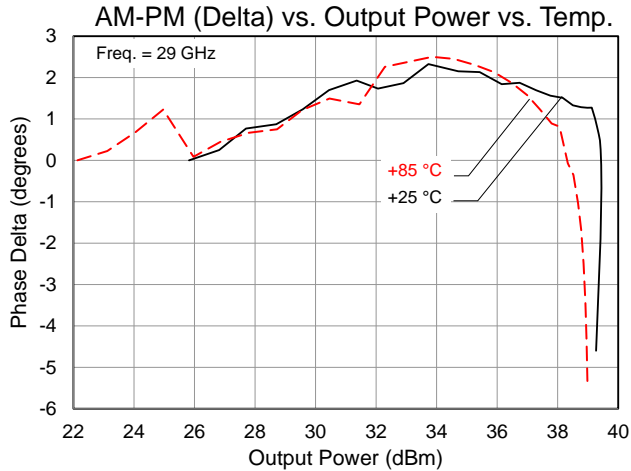
Typical Performance – Large Signal

Conditions unless otherwise specified: $V_D = +20\text{ V}$, $I_{DQ} = 560\text{ mA}$, $V_G = -2.5\text{ V}$ typical, CW.



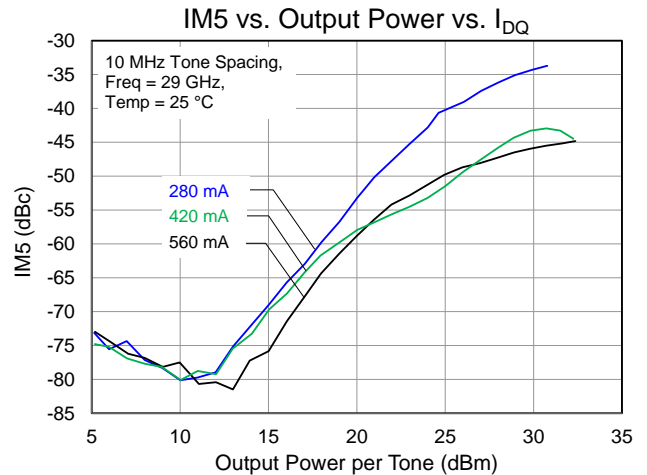
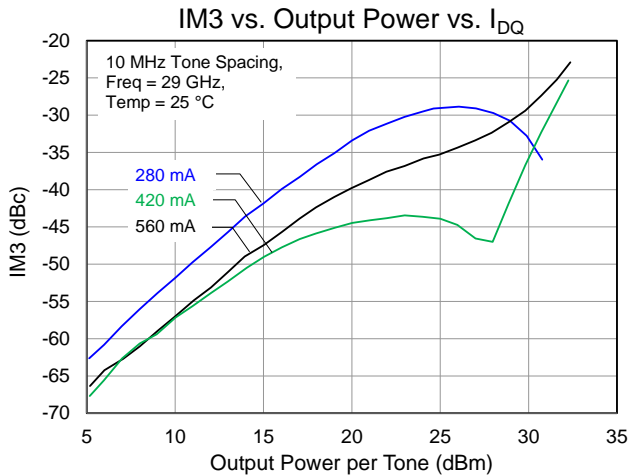
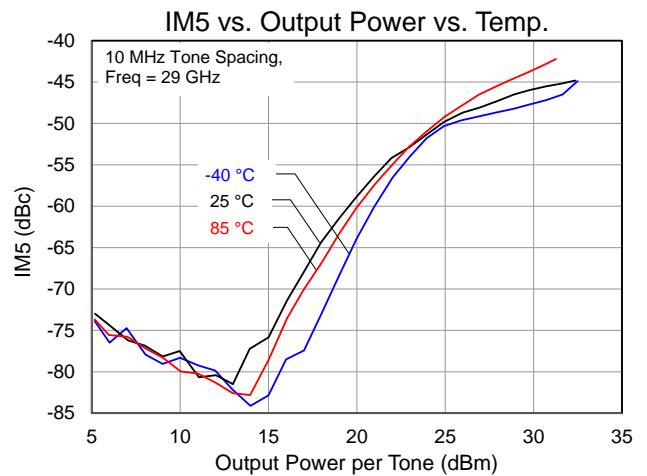
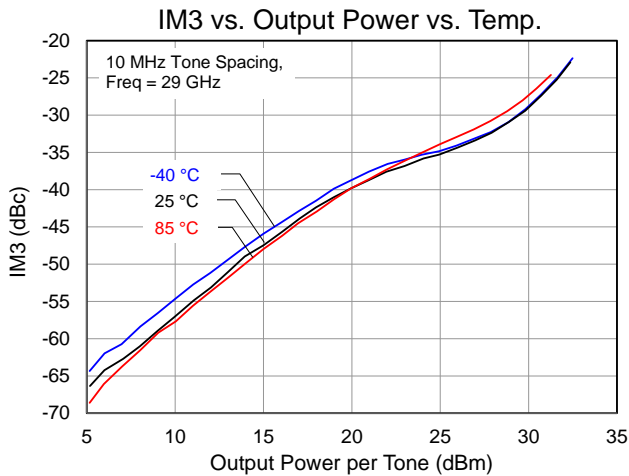
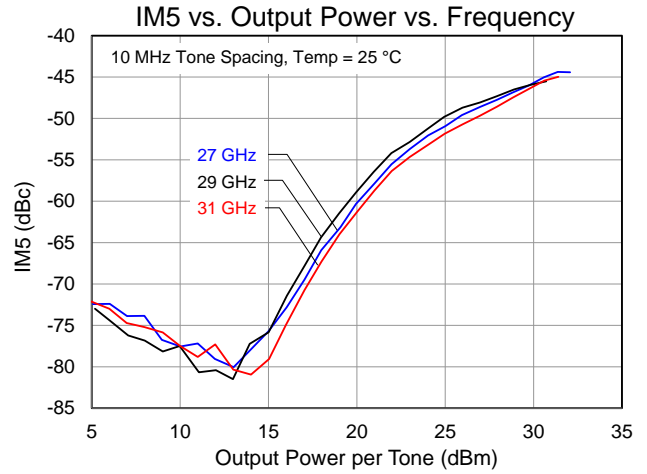
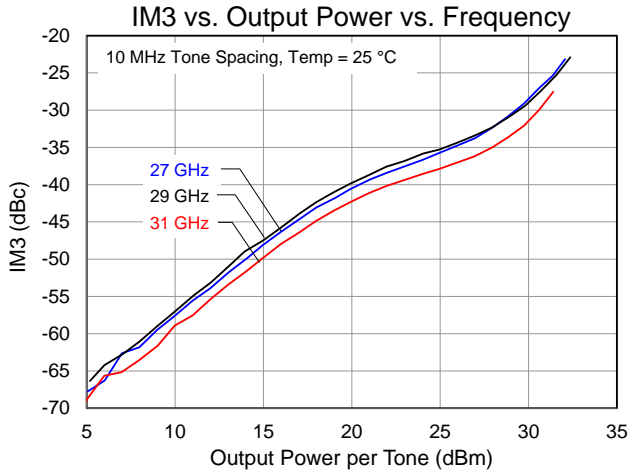
Performance Plots – Large Signal

Conditions unless otherwise specified: $V_D = +20\text{ V}$, $I_{DQ} = 560\text{ mA}$, $V_G = -2.5\text{ V}$ typical, CW.



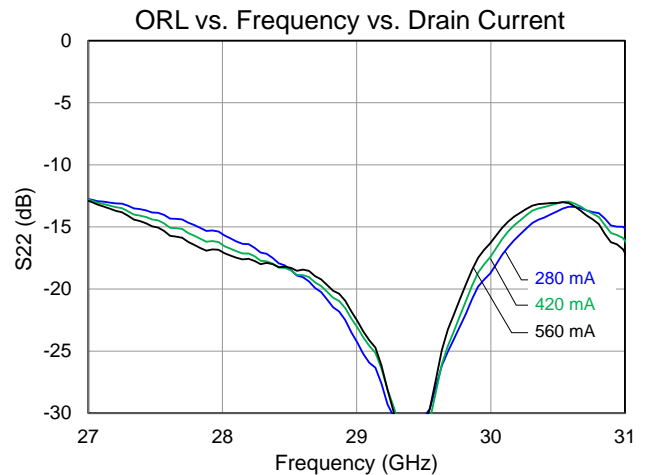
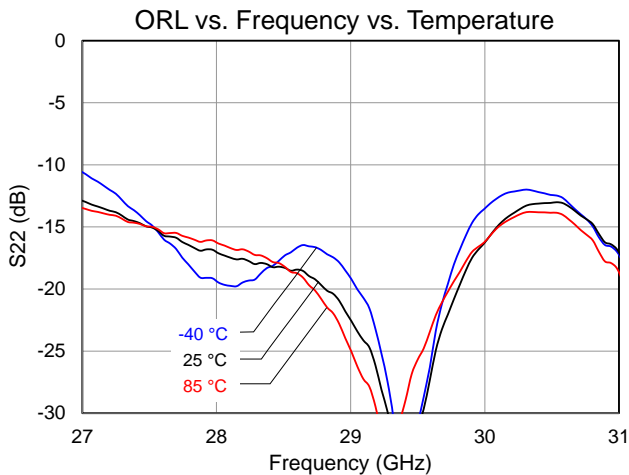
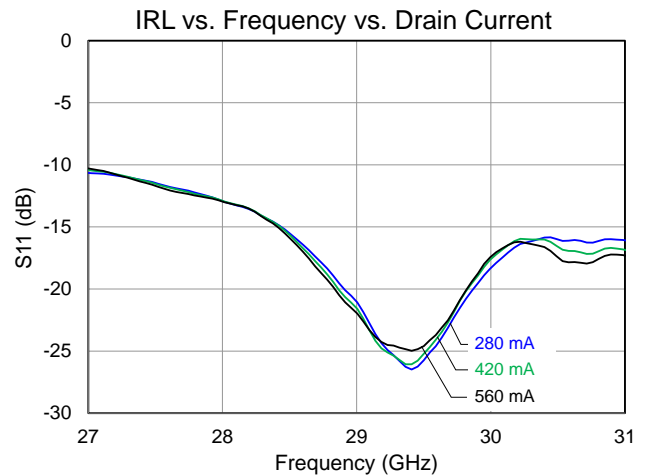
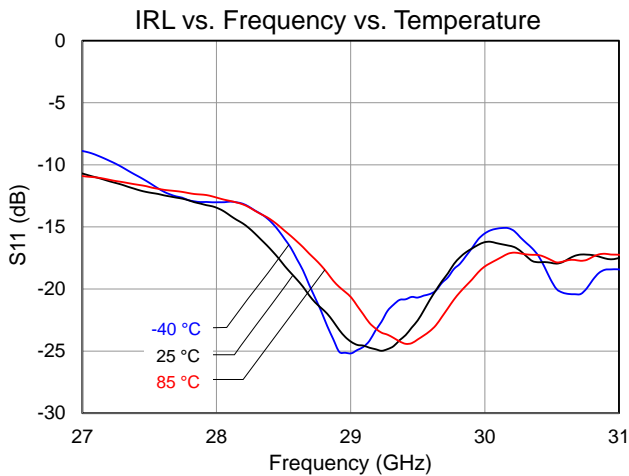
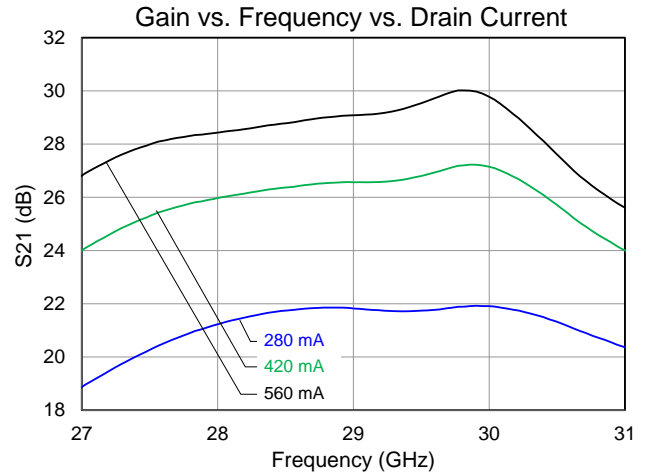
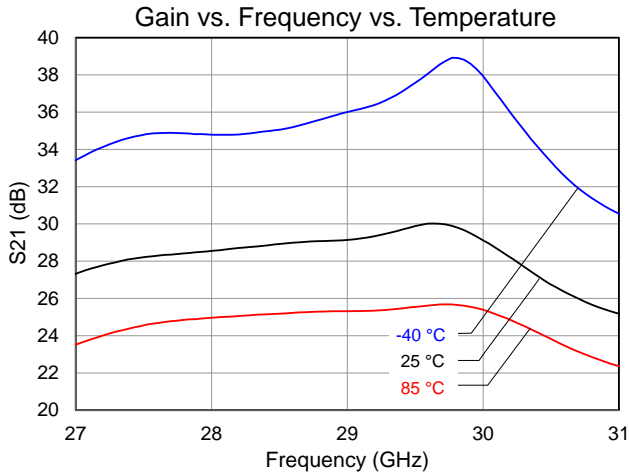
Typical Performance – Linearity

Conditions unless otherwise specified: $V_D = +20\text{ V}$, $I_{DQ} = 560\text{ mA}$, $V_G = -2.5\text{ V}$ typical, CW.



Typical Performance – Small Signal

Conditions unless otherwise specified: $V_D = +20\text{ V}$, $I_{DQ} = 560\text{ mA}$, $V_G = -2.5\text{ V}$ typical, CW.



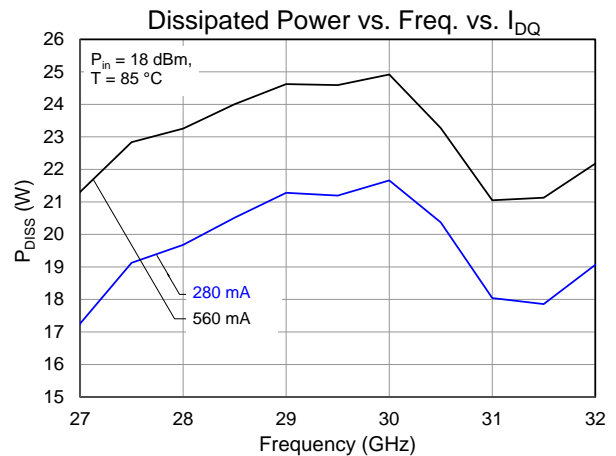
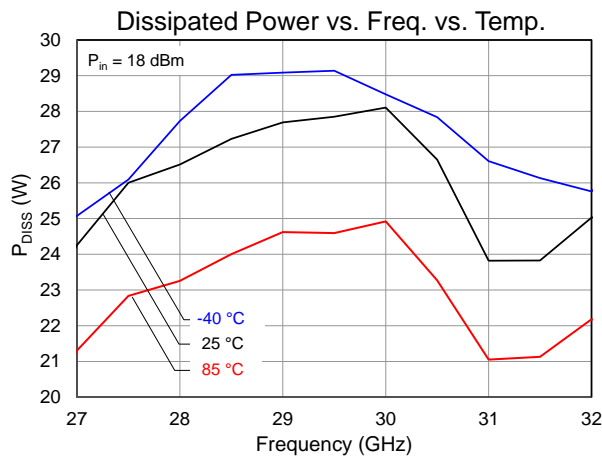
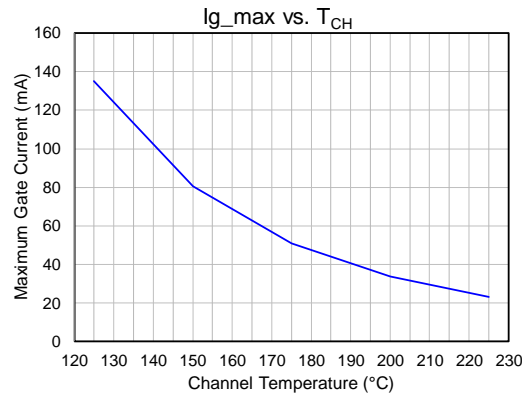
Thermal and Reliability Information

Parameter	Test Conditions	Value	Units
Thermal Resistance (θ_{JC}) ⁽¹⁾	CW, $V_D = +20\text{ V}$, $I_{DQ} = 560\text{ mA}$,	2.23	$^{\circ}\text{C}/\text{W}$
Channel Temperature (T_{CH}) (Quiescent) ⁽²⁾	$T_{BASE} = 85\text{ }^{\circ}\text{C}$ $P_{DISS} = 11.2\text{ W}$	110	$^{\circ}\text{C}$
Thermal Resistance (θ_{JC}) ⁽¹⁾	$V_D = +20\text{ V}$, $I_{DQ} = 280\text{ mA}$, $T_{BASE} = 85\text{ }^{\circ}\text{C}$,	2.40	$^{\circ}\text{C}/\text{W}$
Channel Temperature (T_{CH}) (under RF) ⁽²⁾	Freq = 30 GHz, $P_{IN} = 18\text{ dBm}$, $P_{OUT} = 37.2\text{ dBm}$, $P_{DISS} = 21.7\text{ W}$, $I_{D_Drive} = 1.38\text{ A}$	137	$^{\circ}\text{C}$
Thermal Resistance (θ_{JC}) ⁽¹⁾	$V_D = +20\text{ V}$, $I_{DQ} = 560\text{ mA}$, $T_{BASE} = 85\text{ }^{\circ}\text{C}$,	2.45	$^{\circ}\text{C}/\text{W}$
Channel Temperature (T_{CH}) (RF drive) ⁽²⁾	Freq = 30 GHz, $P_{IN} = 18\text{ dBm}$, $P_{OUT} = 38.3\text{ dBm}$, $P_{DISS} = 24.9\text{ W}$, $I_{D_Drive} = 1.58\text{ A}$	146	$^{\circ}\text{C}$

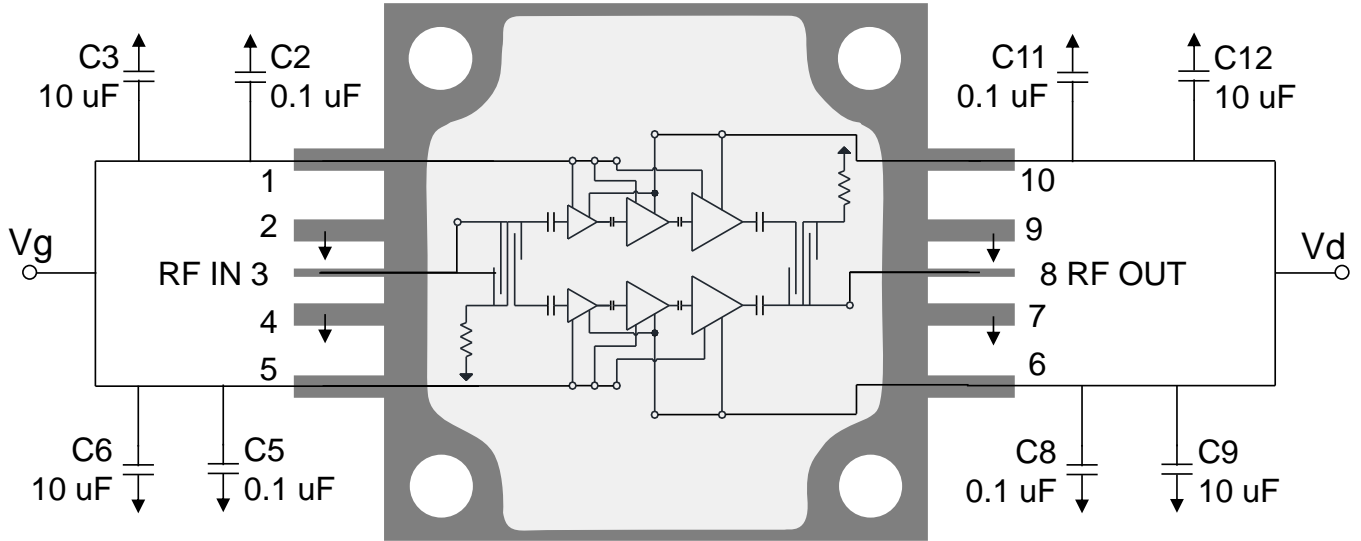
Notes:

1. Thermal resistance is referenced to the back of package ($85\text{ }^{\circ}\text{C}$)
2. Refer to the following document: [GaN Device Channel Temperature, Thermal Resistance, and Reliability Estimates](#)

Dissipated Power and Maximum Gate Current



Applications Information and Pin Layout



Bias Up Procedure

1. Set I_D limit to 2 A, I_G limit to 35 mA
2. Apply -5 V to V_G
3. Apply $+20\text{ V}$ to V_D ; ensure I_{DQ} is approx. 0 mA
4. Adjust V_G until $I_{DQ} = 560\text{ mA}$ ($V_G \sim -2.5\text{ V Typ.}$).
5. Turn on RF supply

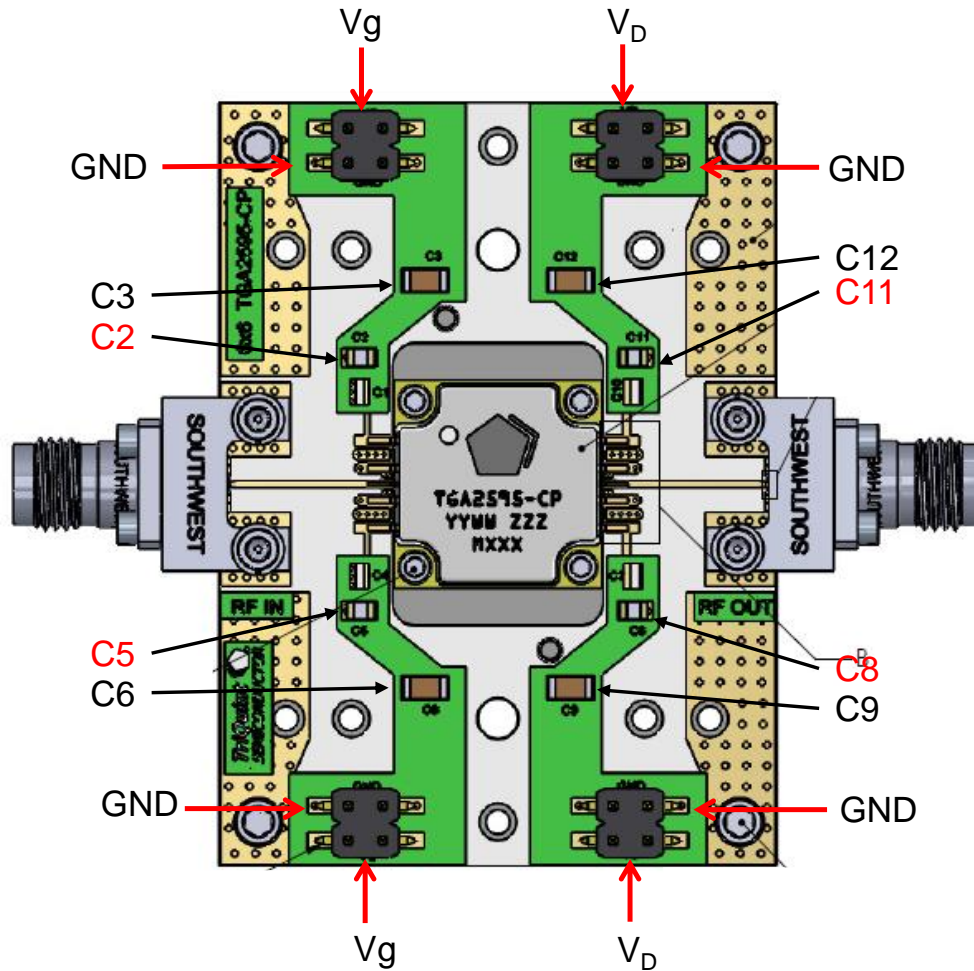
Bias Down Procedure

1. Turn off RF supply
2. Reduce V_G to -5 V ; ensure I_{DQ} is approx. 0 mA
3. Set V_D to 0 V
4. Turn off V_D supply
5. Turn off V_G supply

Pin Description

Pad No.	Symbol	Description
1,5	V_G	Gate Voltage; Bias network is required; must be biased from both sides; see recommended Application Information above.
3	RF_{IN}	Input; matched to $50\ \Omega$; DC blocked
2,4,7,9	GND	Must be grounded on the PCB.
6,10	V_D	Drain voltage; Bias network is required; must be biased from both sides; see recommended Application Information above.
8	RF_{OUT}	Output; matched to $50\ \Omega$; DC blocked

Assembly Drawing



PCB NOTES:

- (1) Both Top and Bottom V_d and V_g must be biased.
- (2) This PCB is non-standard, and requires PCB trace modification for 30 GHz performance optimization. See Gerber files for detailed information.

Bill of Materials

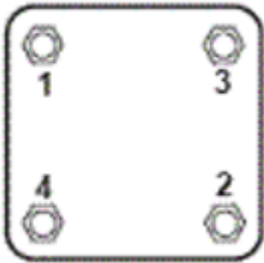
Reference Des.	Value	Description	Manuf.	Part Number
C2, C5, C8, C11	0.1 μ F	Cap, 0603, +50 V, 10 %, X7R	Various	–
C3, C6, C9, C12 ⁽¹⁾	10 μ F	Cap, 1206, +50 V, 20 %, X5R	Various	–

Notes:

1. Capacitors in drain path should be removed for pulsed operation.

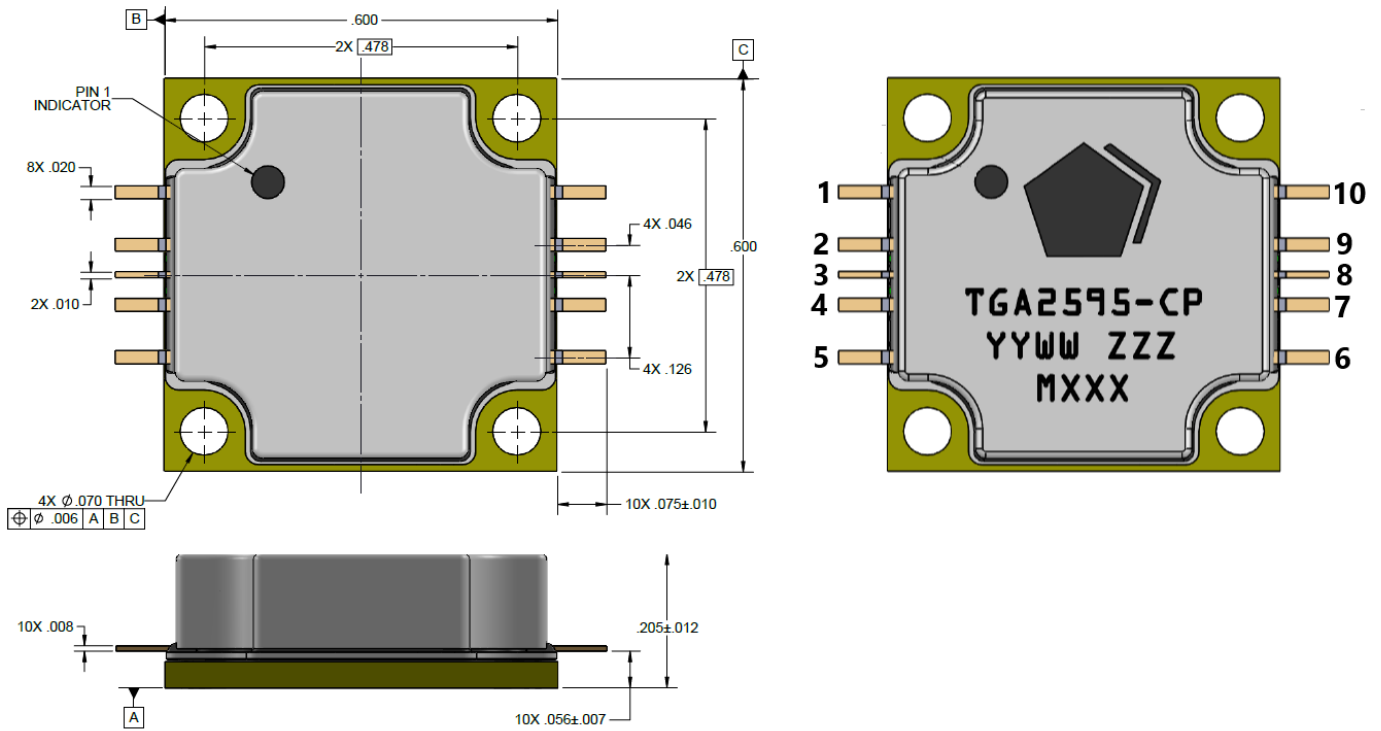
Assembly Notes

1. Carefully clean the PC board and package leads with alcohol. Allow it to dry fully.
2. To improve the thermal and RF performance, Qorvo recommends attaching a heat sink to the bottom of the PCB and apply thermal compound (Arctic Silver 5 recommended) or 4 mil indium shim between the heat sink and the package.
3. (The following is for *information only*. There are many variables in a second level assembly that Qorvo does not control, so Qorvo does not recommend an absolute torque value.) Use screws to attach the component to the heat sink. A suggested torque value is 16 in-oz. for a 0-80 screw. Start with screws finger tight, then torque to 8 in-oz., then torque to final value. Use the following tightening pattern:



4. Apply no-flux solder to each pin of the TGA2595-CP. The component leads should be manually soldered, and the package cannot be subjected to conventional reflow processes. The use of no-clean solder to avoid washing after soldering is recommended.

Mechanical Information and Marking



Units: inches

Tolerances unless specified: x.xxx = ± 0.005

Materials:

Base: Copper

Lead: Alloy 194

Lid: Plastic

All metalized features are gold plated

Part is epoxy sealed

Marking:

2595: Part number

YY: Part Assembly year

WW: Part Assembly week

ZZZ: Serial Number

MXXX: Batch ID

Handling Precautions

Parameter	Rating	Standard
ESD – Human Body Model (HBM)	Class 1A	ANSI/ESD/JEDEC JS-001
ESD – Charge Device Model (CDM)	Class C2	JESD22-C101
MSL – Moisture Sensitivity Level	N/A	Blank, null, no content



Caution!
ESD-Sensitive Device

Solderability

Compatible with the latest version of J-STD-020, Lead-free solder, 260 °C

RoHS Compliance

This product is compliant with the 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment), as amended by Directive 2015/863/EU. This product also has the following attributes:

- Lead Free
- Halogen Free (Chlorine, Bromine)
- Antimony Free
- TBBP-A (C₁₅H₁₂Br₄O₂) Free
- PFOS Free
- SVHC Free

Contact Information

For the latest specifications, additional product information, worldwide sales and distribution locations:

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Tel: 1-844-890-8163

Email: customer.support@qorvo.com

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